

Sidewalls formed by the crust may be removed during the stripping of the resist or may be removed using a separate wet stripping as described in U.S. Patent [Application No. \_\_\_\_\_ (Attorney Docket Number LAM1P156)] No. 6,413,877 entitled "Method of Preventing Damage To Organo-Silicate-Glass Materials During Resist Stripping" by Rao Anapragada, with the same filing date, and which is incorporated by reference."

**In The Abstract:**

Please amend the abstract as follows:

**ABSTRACT**

"A [method of etching a stack using a fluorine containing gas and an ammonia containing gas is provided. Generally, the stack is placed in a plasma processing chamber. A fluorine containing gas is flowed into the plasma processing chamber. An ammonia containing gas is flowed into the plasma processing chamber. A plasma is generated. The stack is then etched.

In addition, a] device for etching stacks on a substrate is provided. The device comprises: a plasma chamber with chamber walls; a plasma confinement device for reducing plasma contact with the chamber walls; a gas source; plasma generation and energizing device; and an exhaust system for pumping plasma away. The gas source comprises a fluorine containing gas source and an ammonia containing gas source."

**In The Claims:**

Please amend the claims 3 and 13-18 and add claim 19, as follows:

3. (Once Amended) The apparatus, as recited in claim 2, wherein [the] a stack comprises a layer with a low dielectric constant material and an etch stop layer.

[14] 13. (Once Amended) The apparatus, as recited in claim 1, wherein the plasma confining device comprises a plurality of spaced apart plasma rings.

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[15] 14. (Once Amended) The apparatus, as recited in claim [14] 13, wherein the exhaust system is able to maintain a pressure below 300 mTorr within the chamber walls.

[16] 15. (Once Amended) A method of etching a stack, comprising:

- placing the stack in a plasma processing chamber;
- flowing a fluorine containing gas into the plasma processing chamber;
- flowing an ammonia containing gas into the plasma processing chamber;
- generating a plasma; and
- etching the stack.

[17] 16. (Once Amended) The method, as recited in claim [11] 15, further comprising confining the plasma to reduce plasma contact with chamber walls.

[18] 17. (Once Amended) The method, as recited in claim [12] 15, wherein the stack comprises a low dielectric constant layer and an etch stop layer over a substrate.

[19] 18. (Once Amended) The method, as recited in claim [17] 16, wherein the fluorine containing gas and the ammonia containing gas are provided in an alternating manner and wherein a plasma is generated from the fluorine containing gas and a plasma is generated from the ammonia containing gas.

19. (New) The apparatus, as recited in claim 1, wherein the plasma confinement device is able to confine the plasma and prevent defects from the formation of particles from ammonia and fluorine.

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